

STARPOWER

SEMICONDUCTOR

IGBT

GD10FFK120C5SP

1200V/10A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

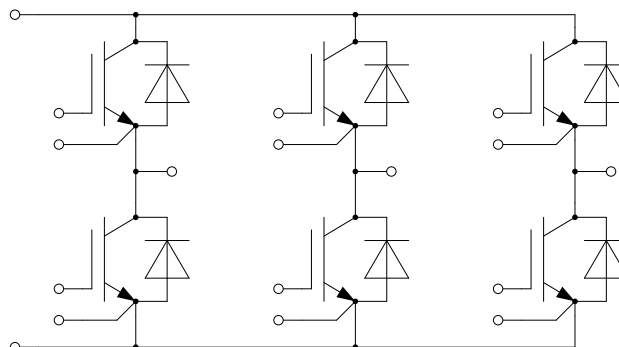
- NPT IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 150°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	20	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	116	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.15	2.60	V	
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.65			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.1	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			/		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.65		nF	
C_{res}	Reverse Transfer Capacitance				0.04		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.11		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		164		ns	
t_r	Rise Time			54		ns	
$t_{d(off)}$	Turn-Off Delay Time			238		ns	
t_f	Fall Time			352		ns	
E_{on}	Turn-On Switching Loss			2.18		mJ	
E_{off}	Turn-Off Switching Loss			0.72		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		168		ns
t_r	Rise Time				55		ns
$t_{d(off)}$	Turn-Off Delay Time			247		ns	
t_f	Fall Time			438		ns	
E_{on}	Turn-On Switching Loss			2.48		mJ	
E_{off}	Turn-Off Switching Loss			0.97		mJ	
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$			80		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.05		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		0.7		μC
I_{RM}	Peak Reverse Recovery Current			7		A
E_{rec}	Reverse Recovery Energy			0.31		mJ
Q_r	Recovered Charge			1.4		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		9		A
E_{rec}	Reverse Recovery Energy			0.51		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		60		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		8.00		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			1.076	K/W
	Junction-to-Case (per Diode)			1.713	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.195		K/W
	Case-to-Heatsink (per Diode)		0.311		
	Case-to-Heatsink (per Module)		0.020		
M	Mounting Screw:M5	3.0		6.0	N.m
G	Weight of Module		200		g

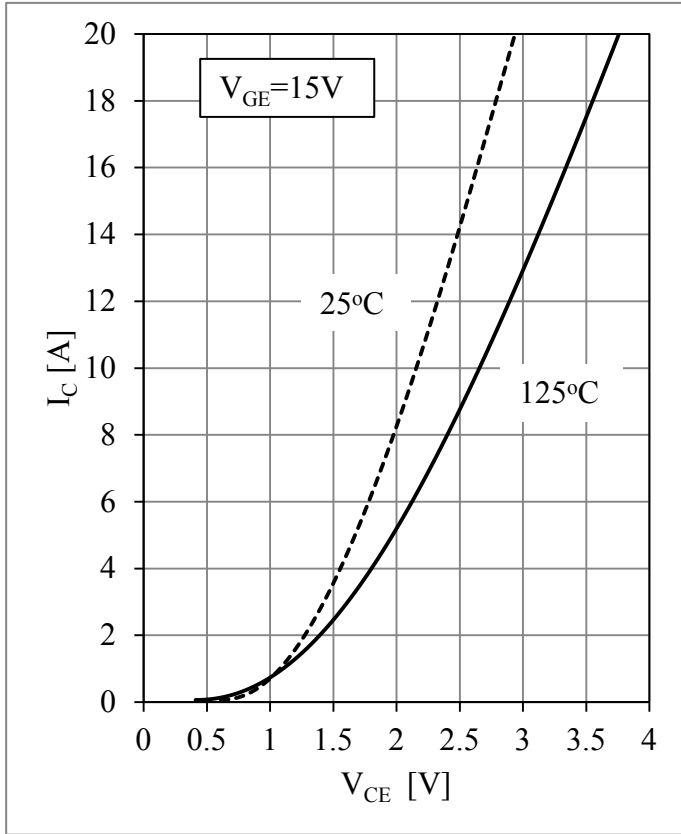


Fig 1. IGBT Output Characteristics

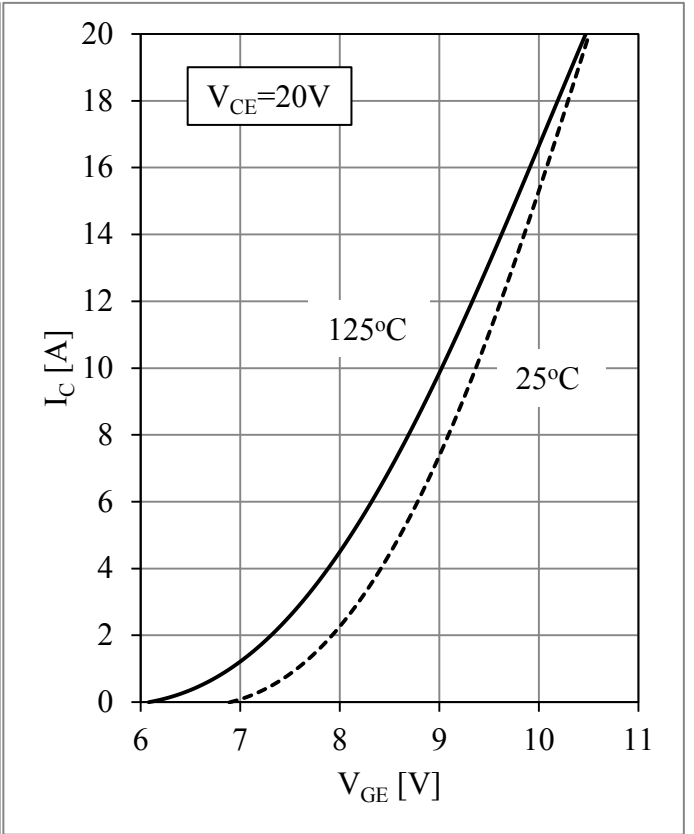


Fig 2. IGBT Transfer Characteristics

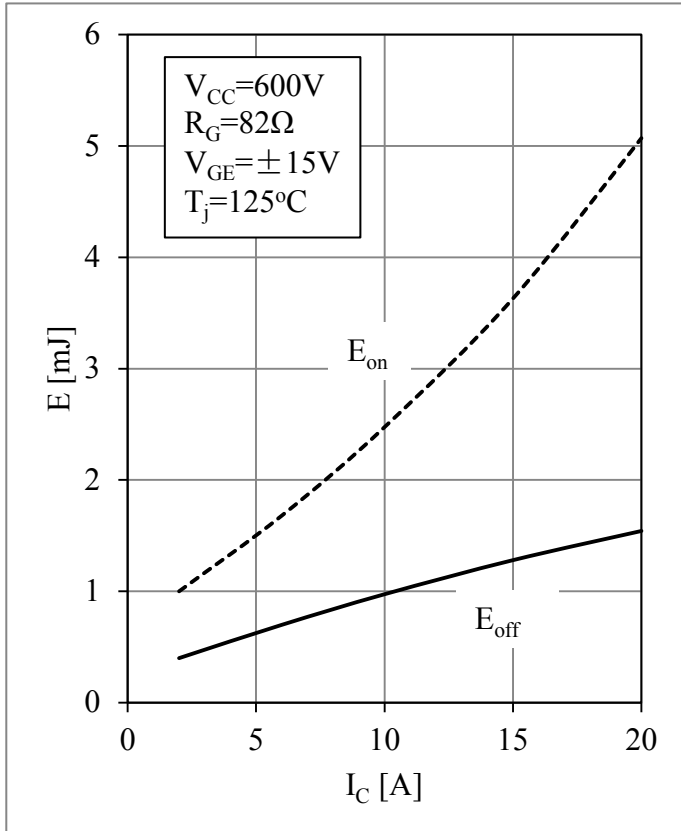


Fig 3. IGBT Switching Loss vs. I_C

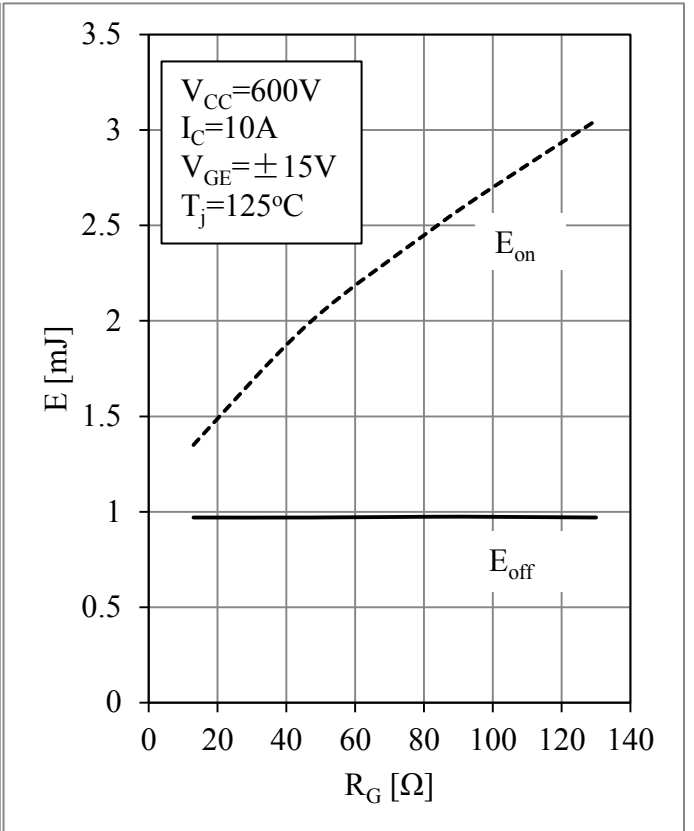


Fig 4. IGBT Switching Loss vs. R_G

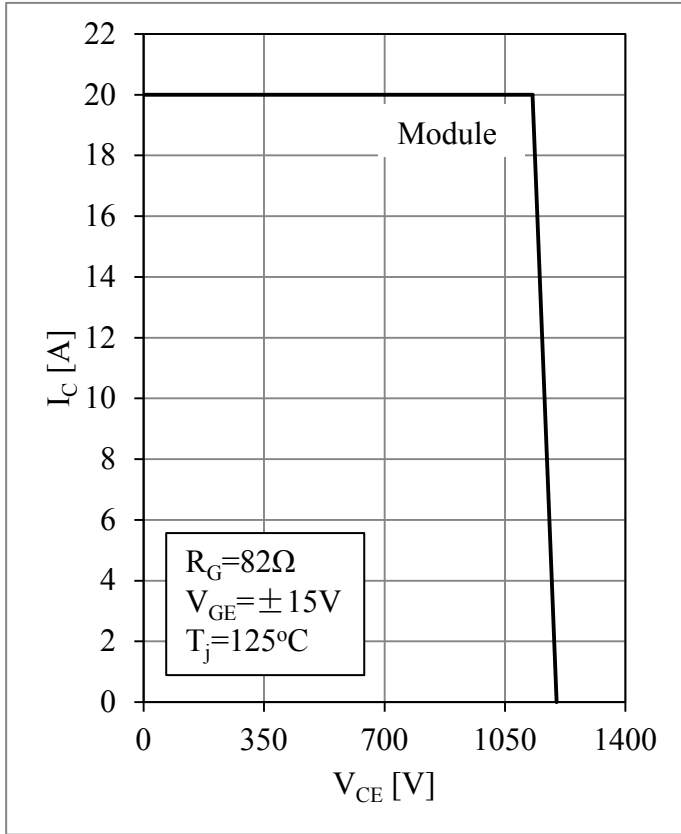


Fig 5. IGBT RBSOA

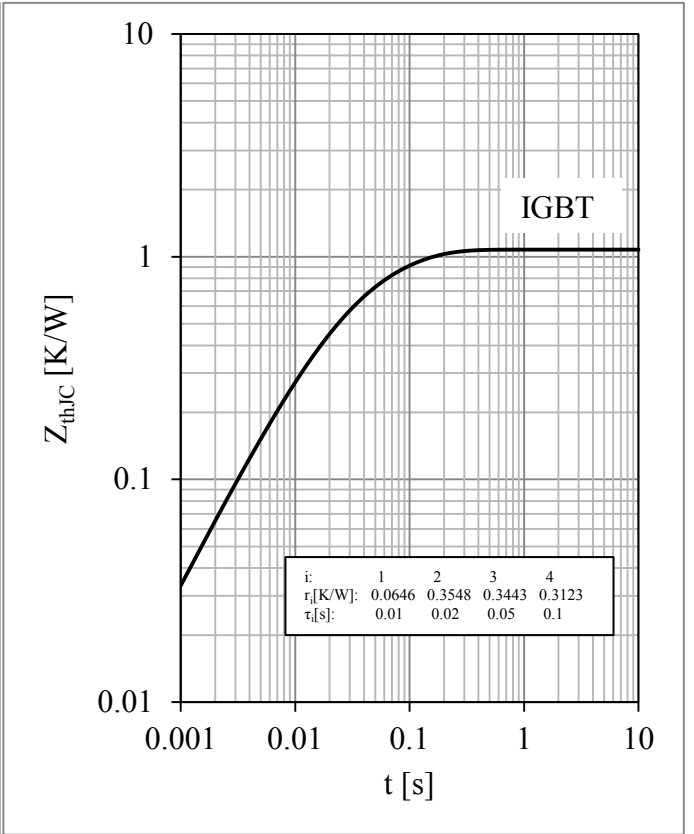


Fig 6. IGBT Transient Thermal Impedance

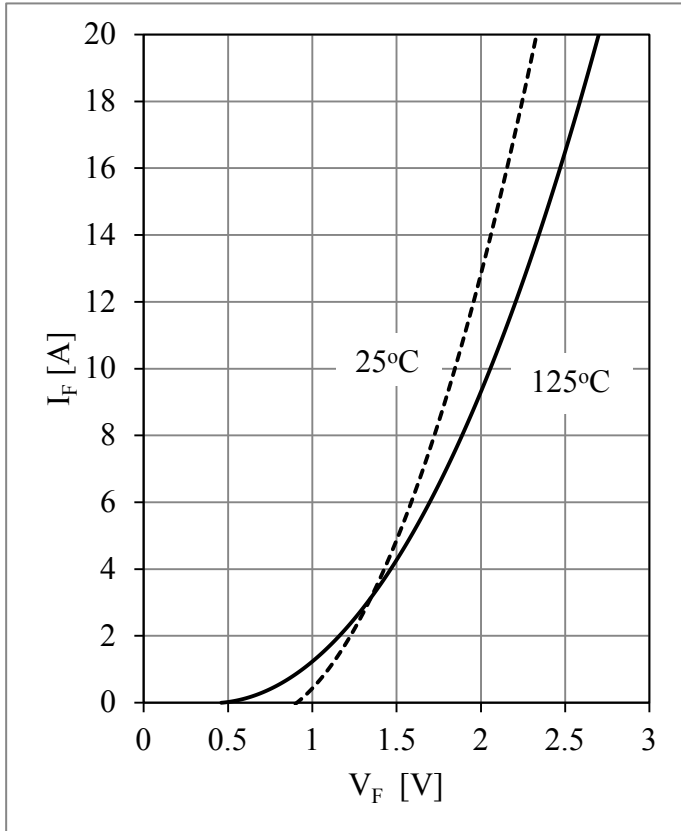


Fig 7. Diode Forward Characteristics

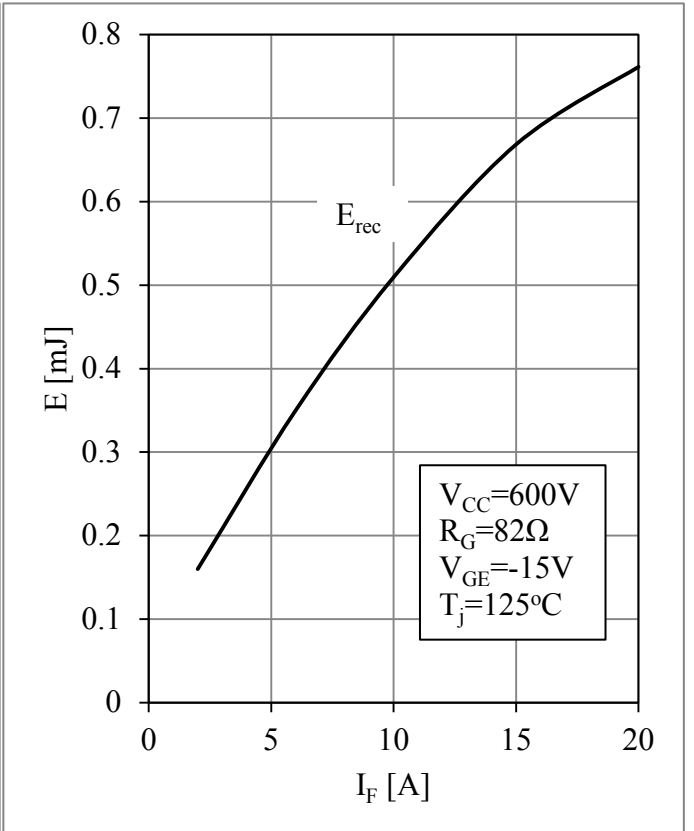


Fig 8. Diode Switching Loss vs. I_F

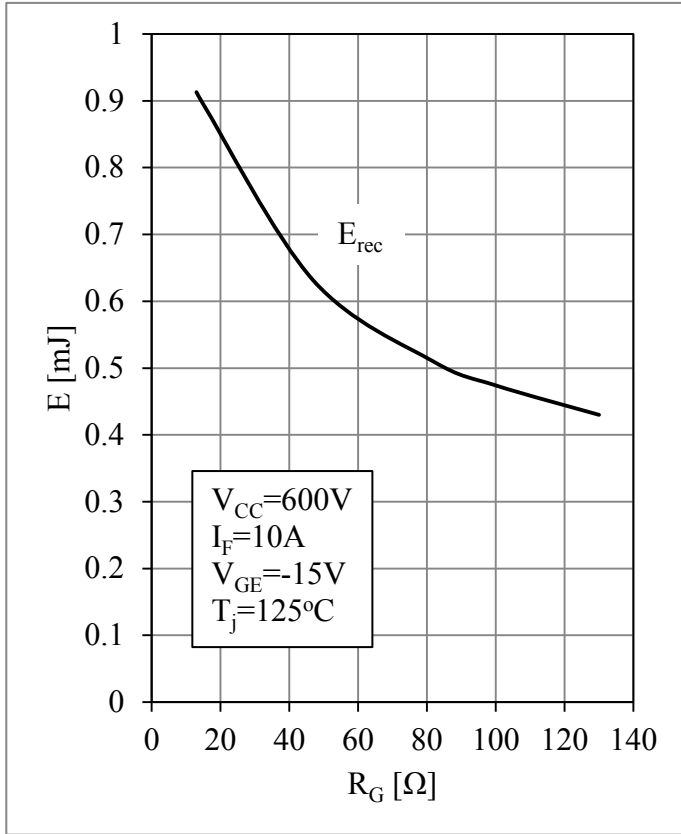


Fig 9. Diode Switching Loss vs. R_G

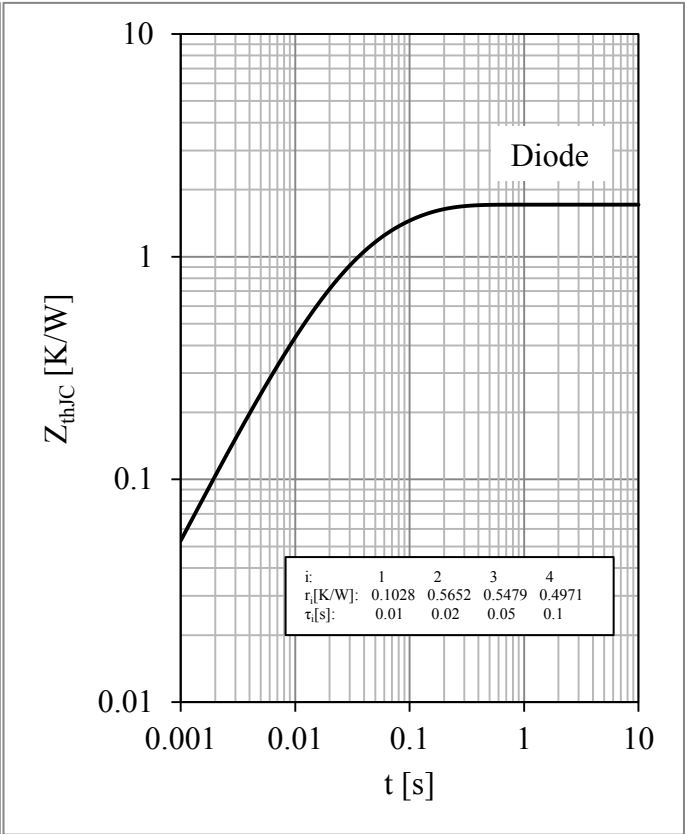
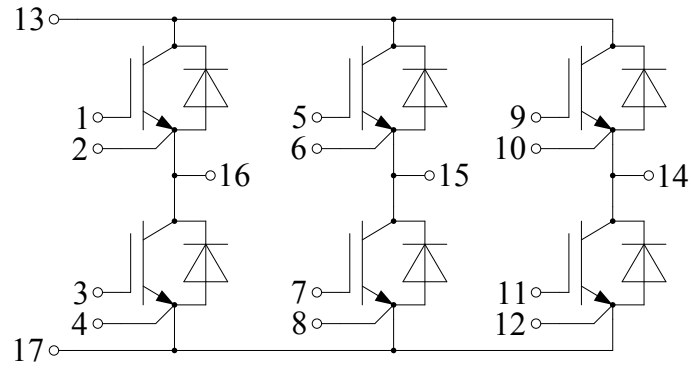


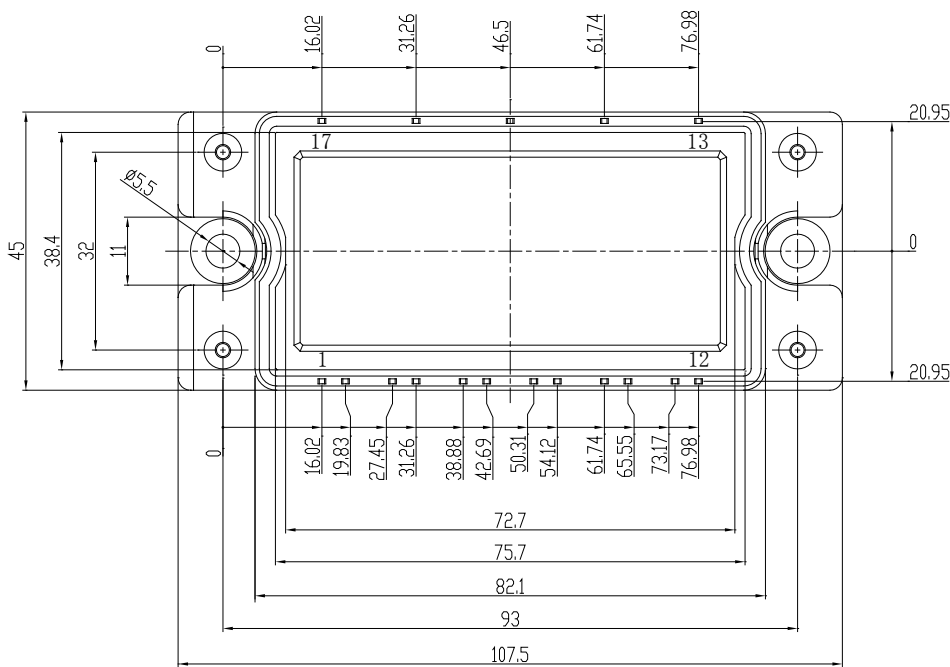
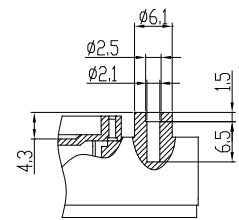
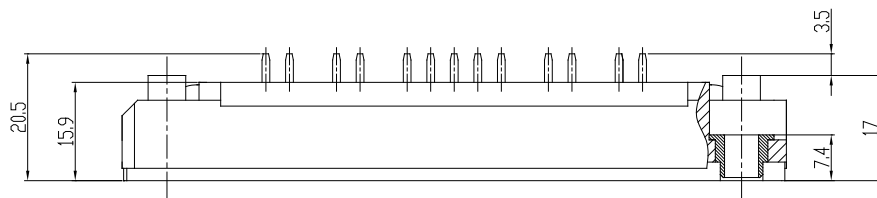
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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